## EPHTAXXY OF MAY COMPOUND SEMICONDUCTOR

## EPITAXXY OF MEV COMPOUND SEMICONDUCTOR

Patent Number:

JP62171999

Publication date:

1987-07-28

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Requested Patent:

JP62171999

Application Number: JP19860013751 19860127

Priority Number(s):

IPC Classification:

C30B29/40; C30B23/08; C30B25/02

EC Classification:

EC Classification:

Equivalents:

## Abstract

PURPOSE:A group-IV elementary semiconductor layer of the same as or different from the base semiconductor is allowed to grow epitaxially on the base surface, then a single atomic layer of a group V element is formed thereon, and a III-V compound semiconductor from the group V element used is allowed to grow thereon epitaxially whereby a high-purity semiconductor layer of III-V compound is formed.

CONSTITUTION: A Si crystal of <100> or <111> face orientation is used as a IV-group semiconductor base, and a group-IV semiconductor layer 2 the same as or different from the base such as Si or Ge is allowed to grow epitaxially so that the thickness of the layer becomes integral times that corre sponding to double atom layer of the semiconductor. Then, a single atom layer 3 of group-V element such as P is formed by adsorption on its surface, further, a semiconductor layer 4 of III-V compound from the group V element used such as GaP is formed epitaxially thereon. The process enables the economical mass-production of high-quality III-V compound semiconductor layers free from antiphase boundary.